UTC UNISONIC TECHNOLOGIES CO., LTD

UT4392 **Power MOSFET**

30V N-CHANNEL POWER MOSFET

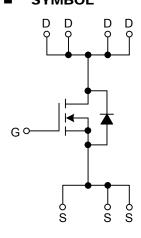
DESCRIPTION

The UT4392 uses UTC advanced technology to provide excellent R_{DS(ON)}, low gate charge and operation with low gate voltages. This device is suitable for being used in such applications: high-Side DC/DC Conversion, notebook and sever.

FEATURES

- * $V_{DS}(V)=30V$
- * I_D=12.5 A (V_{GS}=10V)
- * High Density Cell Design for Ultra Low On-resistance
- * $R_{DS(ON)}$ <11.5m Ω @ V_{GS} =10V
- * $R_{DS(ON)}$ <16.5m Ω @ V_{GS} =4.5V

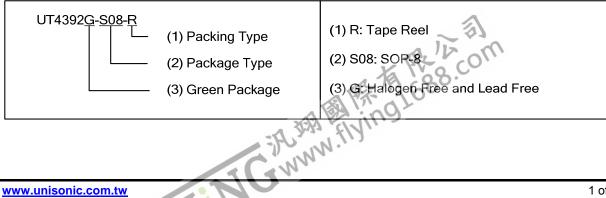
SYMBOL

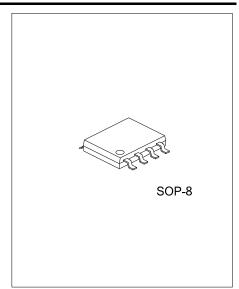


ORDERING INFORMATION

Ordering Number	Package	Pin Assignment							Da alsia a	
		1	2	3	4	5	6	7	8	Packing
UT4392G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

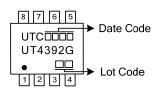
Note: Pin Assignment: G: Gate D: Drain S: Source





www.unisonic.com.tw 1 of 5

MARKING





ABSOLUTE MAXIMUM RATINGS (T_A =25°C, unless otherwise specified.)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current	I _D	12.5	Α
Pulsed Drain Current	I _{DM}	50	Α
Power Dissipation(T _A =25°C)	P_D	3.0	W
Junction Temperature	TJ	+150	°C
Storage Temperature	T _{STG}	-55 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient (PCB mounted)	θ_{JA}			50	°C/W
Junction to Case	θ _{JC}			25	°C/W

Notes: 1. Pulse width limited by the Maximum junction temperature.

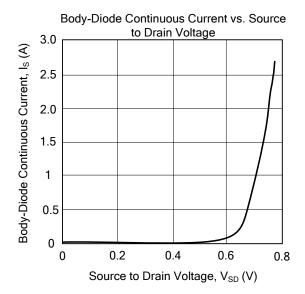
2. Surface Mounted on FR4 Board, t ≤ 10 sec.

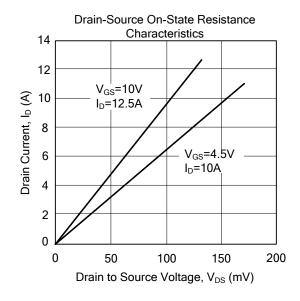
ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified.)

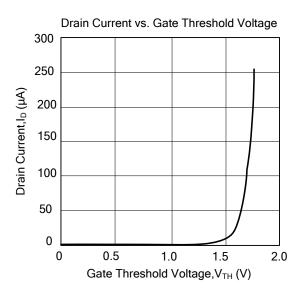
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V	
Drain-Source Leakage Current	I _{DSS}	V _{DS} =24 V, V _{GS} =0 V			1.0	μΑ	
Gate-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA	
ON CHARACTERISTICS							
Gate-Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_{DS} = 250 \mu A$	1	1.8	3	V	
On State Drain Current (Note 1)	I _{D(ON)}	V _{DS} ≥ 5V, V _{GS} = 10V	30			Α	
Static Drain-Source On-Resistance(Note 1)	R _{DS(ON)}	V _{GS} =10 V, I _D =12.5 A V _{GS} =4.5 V, I _D =10 A		9 13	11.5 16.5	mΩ mΩ	
DYNAMIC PARAMETERS		VGS -4.5 V, ID - 10 A		10	10.5	11122	
Input Capacitance	C _{ISS}	V _{DS} =15 V, V _{GS} =0 V, -f=1.0MHz, (Note 2)		2134		pF	
Output Capacitance	Coss			343		pF	
Reverse Transfer Capacitance	C _{RSS}			134		pF	
SWITCHING PARAMETERS	- 1100	1	<u> </u>			<u> </u>	
Total Gate Charge	Q_{G}	-V _{DS} =15V, V _{GS} =10 V,		26		nC	
Gate Source Charge	Q _{GS}			6		nC	
Gate Drain Charge	Q_{GD}	I _D =12.5A, (Note 2)		5		nC	
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =15V,I _D =1 A,V _{GEN} =10 V		17		ns	
Turn-ON Rise Time	t _R			3.5		ns	
Turn-OFF Delay Time	t _{D(OFF)}	$R_G=6 \Omega$, $R_L=15 \Omega$, (Note 3)		40		ns	
Turn-OFF Fall-Time	t _F	1		6		ns	
SOURCE- DRAIN DIODE RATINGS AND C	HARACTER	RISTICS			•		
Diode Forward Voltage	V_{SD}	I _S =2.7 A, V _{GS} =0V		0.85	1.3	V	
Maximum Body-Diode Continuous Current					2.7	Α	
Maximum Body-Diode Continuous Current Notes: 1. Pulse Test: PW ≤300µS, Duty Cyc 2. For DESIGN AID ONLY, not subje 3. Switching time is essentially indep 4. Pulse width limited by the Maximu 5. Surface Mounted on FR4 Board, t	cle ≤2% ect to produce pendent of op m junction to ≤ 10 sec.	ction testing. perating temperature. emperature.	<i>U</i> ,				
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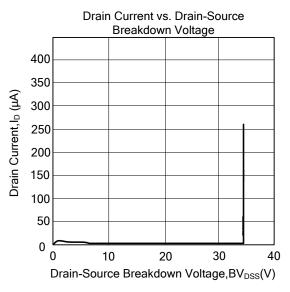
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TYPICAL CHARACTERISTICS









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